

## ABSTRACT

There is provided a technology for obtaining an electrode having a low  
5 contact resistance and less surface roughness. There is provided an  
electrode comprising a semiconductor film 101, and a first metal layer 102  
and a second metal layer 103 sequentially stacked in this order on the  
semiconductor film 101, characterized in that the first metal film 102 is  
formed of Al, and the second metal film 103 is formed of at least one metal  
10 selected from the group consisting of Nb, W, Fe, Hf, Re, Ta and Zr.